

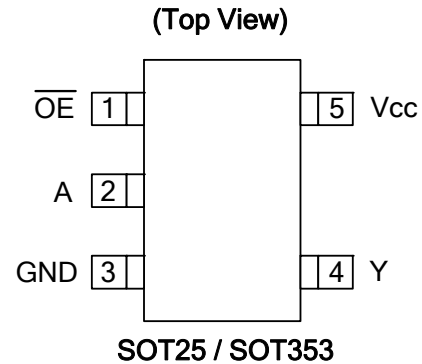
74AHC1G125

SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Description

The 74AHC1G125 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a HIGH-level is applied to the output enable (\overline{OE}) pin. The device is designed for operation with a power supply range of 2.0V to 5.5V.

Pin Assignments



Features

- Supply Voltage Range from 2.0V to 5.5V
- ± 8 mA Output Drive at 5.0V
- CMOS low power consumption
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time.
- ESD Protection per JESD 22
 - Exceeds 200-V Machine Model (A115-A)
 - Exceeds 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- SOT25 and SOT353: Assembled with “Green” Molding Compound (no Br, Sb)
- Lead Free Finish / RoHS Compliant (Note 1)

Applications

- General Purpose Logic
- Wide array of products such as:
 - PCs, networking, notebooks, netbooks, PDAs
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box
 - Phones, Personal Navigation / GPS
 - MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

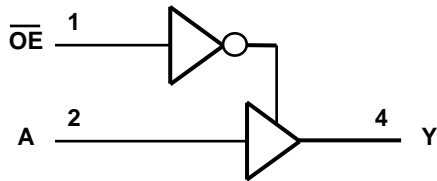
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Pin Descriptions

Pin Name	Pin No.	Description
$\overline{\text{OE}}$	1	Output Enable
A	2	Data Input
GND	3	Ground
Y	4	Data Output
Vcc	5	Supply Voltage

Logic Diagram



Function Table

Inputs		Output
$\overline{\text{OE}}$	A	Y
L	H	H
L	L	L
H	X	Z

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Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
V _I	Input Voltage Range	-0.5 to 6.5	V
V _O	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-20	mA
I _{OK}	Output Clamp Current (V _O < 0 or V _O > V _{CC})	±20	mA
I _O	Continuous output current (V _O = 0 to V _{CC})	±25	mA
I _{CC}	Continuous current through V _{CC}	50	mA
I _{GND}	Continuous current through GND	-50	mA
T _J	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 3)

Symbol	Parameter		Min	Max	Unit
V _{CC}	Operating Voltage		2	5.5	V
V _{IH}	High-level Input Voltage	V _{CC} = 2V	1.5		V
		V _{CC} = 3V	2.1		
		V _{CC} = 5.5V	3.85		
V _{IL}	Low-level input voltage	V _{CC} = 2V		0.5	V
		V _{CC} = 3V		0.9	
		V _{CC} = 5.5V		1.65	
V _I	Input Voltage		0	5.5	V
V _O	Output Voltage		0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 2V		-50	uA
		V _{CC} = 3.3V ± 0.3V		-4	mA
		V _{CC} = 5V ± 0.5V		-8	
I _{OL}	Low-level output current	V _{CC} = 2V		50	uA
		V _{CC} = 5V ± 0.5V		4	mA
		V _{CC} = 3V		8	
Δt/ΔV	Input transition rise or fall rate	V _{CC} = 3.3V ± 0.3V		100	ns/V
		V _{CC} = 5V ± 0.5V		20	
T _A	Operating free-air temperature		-40	125	°C

Notes: 3. Unused inputs should be held at V_{CC} or Ground.

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Electrical Characteristics

Symbol	Parameter	Test Conditions	V _{CC}	25°C			-40°C to 85°C		-40°C to 125°C		Unit
				Min	Typ.	Max	Min	Max	Min	Max	
V _{OH}	High Level Output Voltage	I _{OH} = -50μA	2V	1.9	2		1.9		1.9		V
			3V	2.9	3		2.9		2.9		
			4.5V	4.4	4.5		4.4		4.4		
		I _{OH} = -4mA	3V	2.58			2.48		2.40		
			4.5V	3.94			3.8		3.70		
V _{OL}	Low Level Output Voltage	I _{OL} = 50μA	2V			0.1		0.1		0.1	V
			3V			0.1		0.1		0.1	
			4.5V			0.1		0.1		0.1	
		I _{OL} = 4mA	3V			0.36		0.44		0.55	
			4.5V			0.36		0.44		0.55	
I _I	Input Current	V _I = 5.5V or GND	0 to 5.5V			± 0.1		± 1		± 2	μA
I _{OZ}	Z State Leakage Current	V _O = 0 to 5.5V	5.5V			0.25		2.5		10	μA
I _{CC}	Supply Current	V _I = 5.5V or GND I _O = 0	5.5V			1		10		40	μA
C _i	Input Capacitance	V _I = V _{CC} – or GND	5.5V		2.0	10		10		10	pF
θ _{JA}	Thermal Resistance Junction-to-Ambient	SOT25	(Note 4)		195						°C/W
		SOT353			430						
θ _{JC}	Thermal Resistance Junction-to-Case	SOT25	(Note 4)		58						°C/W
		SOT353			155						

Note: 4. Test conditions for SOT25, and SOT353: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

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Switching Characteristics

$V_{CC} = 3.3V \pm 0.3$ (see Figure 1)

Parameter	From (Input)	TO (OUTPUT)		25°C			-40°C to 85°C		-40°C to 125°C		Unit
				Min	Typ.	Max	Min	Max	Min	Max	
t_{pd}	A	Y	$C_L=15pF$	0.6	4.7	8.0	0.6	9.5	0.6	11.5	ns
			$C_L=50pF$	0.6	6.6	11.5	0.6	13.0	0.6	14.5	ns
t_{en}	\overline{OE}	Y	$C_L=15pF$	0.6	5.0	8.0	0.6	9.5	0.6	10.5	ns
			$C_L=50pF$	0.6	6.9	11.5	0.6	13.0	0.6	14.5	ns
t_{dis}	\overline{OE}	Y	$C_L=15pF$	0.6	6.0	9.7	0.6	11.5	0.6	12.5	ns
			$C_L=50pF$	0.6	8.3	13.2	0.6	15.0	0.6	16.5	ns

$V_{CC} = 5V \pm 0.5V$ (see Figure 1)

Parameter	From (Input)	TO (OUTPUT)		25°C			-40°C to 85°C		-40°C to 125°C		Unit
				Min	Typ.	Max	Min	Max	Min	Max	
t_{pd}	A	Y	$C_L=15pF$	0.6	3.4	5.5	0.6	6.5	0.6	7.0	ns
			$C_L=50pF$	0.6	4.8	7.5	0.6	8.5	0.6	9.5	ns
t_{en}	\overline{OE}	Y	$C_L=15pF$	0.6	3.6	5.1	0.6	6.0	0.6	6.5	ns
			$C_L=50pF$	0.6	6.5	11.4	0.6	13.0	0.6	14.5	ns
t_{dis}	\overline{OE}	Y	$C_L=15pF$	0.6	4.1	6.8	0.6	8.0	0.6	8.5	ns
			$C_L=50pF$	0.6	5.7	8.8	0.6	10.0	0.6	11.0	ns

Operating Characteristics

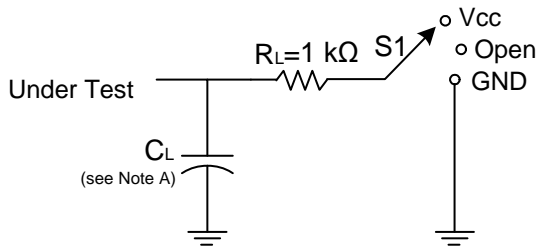
$T_A = 25\text{ }^\circ\text{C}$

Parameter		Test Conditions	$V_{CC} = 5V$	Unit
			Typ.	
C_{pd}	Power dissipation capacitance	f = 1 MHz No Load	12	pF

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Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	Vload
t_{PHZ}/t_{PZH}	GND

V_{CC}	Inputs		V_M	C_L	V_{Δ}
	V_I	t_r/t_f			
$3.3V \pm 0.3V$	V_{CC}	$\leq 3ns$	$V_{CC}/2$	15pF	0.3V
$5V \pm 0.5V$	V_{CC}	$\leq 3ns$	$V_{CC}/2$	15pF	0.3V
$3.3V \pm 0.3V$	V_{CC}	$\leq 3ns$	$V_{CC}/2$	50pF	0.3V
$5V \pm 0.5V$	V_{CC}	$\leq 3ns$	$V_{CC}/2$	50pF	0.3V

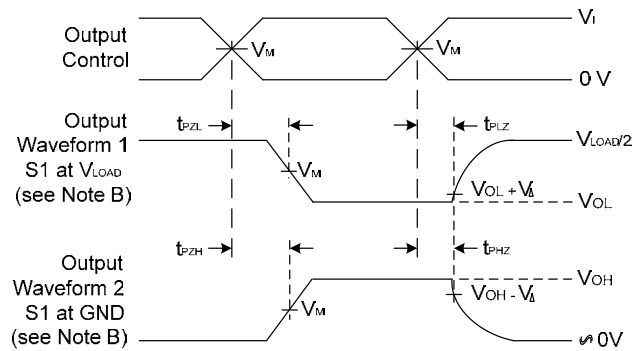
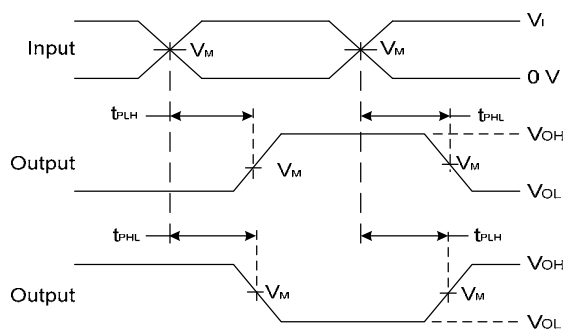
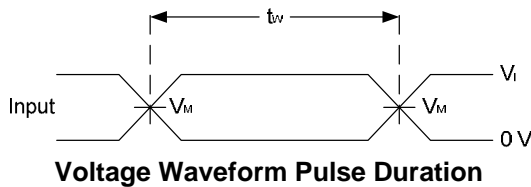


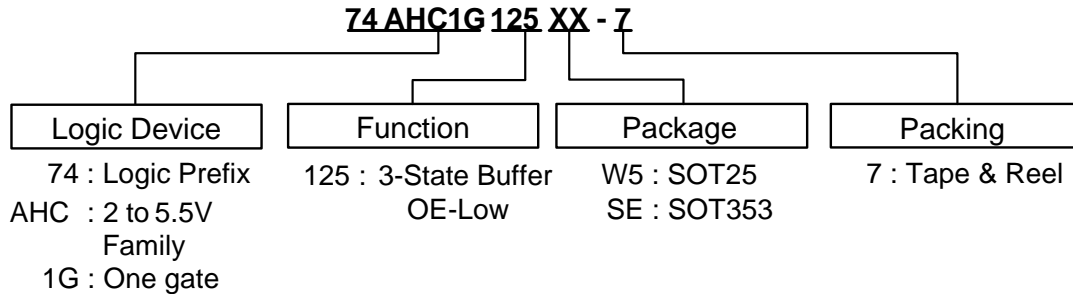
Figure 1. Load Circuit and Voltage Waveforms



- Notes:
- A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate ≤ 1 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - E. t_{PZL} and t_{PZH} are the same as t_{EN} .
 - F. t_{PLH} and t_{PHL} are the same as t_{PD} .

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Ordering Information

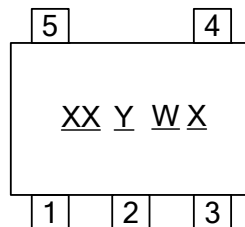


Device	Package Code	Packaging (Note 5)	7" Tape and Reel	
			Quantity	Part Number Suffix
 74AHC1G125W5-7	W5	SOT25	3000/Tape & Reel	-7
 74AHC1G125SE-7	SE	SOT353	3000/Tape & Reel	-7

Notes: 5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Marking Information

(Top View)



XX : Identification code
 Y : Year 0~9
 W : Week : A~Z : 1~26 week;
 a~z : 27~52 week; z represents
 52 and 53 week
 X : A~Z : Internal code

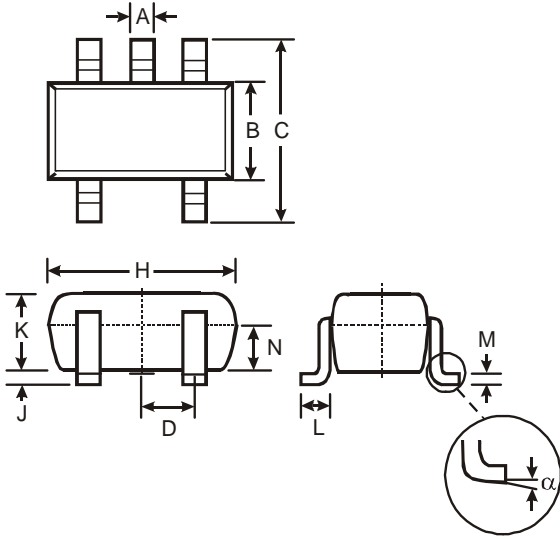
Part Number	Package	Identification Code
74AHC1G125W5	SOT25	YY
74AHC1G125SE	SOT353	YY

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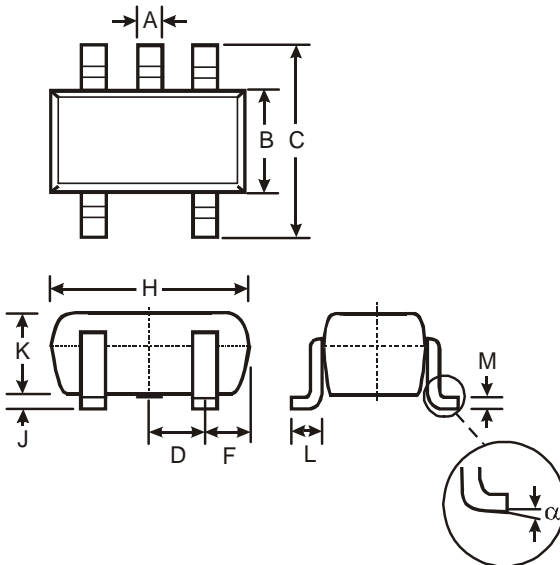
Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



SOT25			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
N	0.70	0.80	0.75
α	0°	8°	—
All Dimensions in mm			

(2) Package Type: SOT353



SOT353		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

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